E. Lattice Semiconductor Corporation - <u>LFE3-95EA-7LFN484C Datasheet</u>



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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	11500
Number of Logic Elements/Cells	92000
Total RAM Bits	4526080
Number of I/O	295
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-95ea-7lfn484c

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ROM Mode

ROM mode uses the LUT logic; hence, Slices 0 through 3 can be used in ROM mode. Preloading is accomplished through the programming interface during PFU configuration.

For more information, please refer to TN1179, LatticeECP3 Memory Usage Guide.

Routing

There are many resources provided in the LatticeECP3 devices to route signals individually or as busses with related control signals. The routing resources consist of switching circuitry, buffers and metal interconnect (routing) segments.

The LatticeECP3 family has an enhanced routing architecture that produces a compact design. The Diamond and ispLEVER design software tool suites take the output of the synthesis tool and places and routes the design.

sysCLOCK PLLs and DLLs

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. The devices in the LatticeECP3 family support two to ten full-featured General Purpose PLLs.

General Purpose PLL

The architecture of the PLL is shown in Figure 2-4. A description of the PLL functionality follows.

CLKI is the reference frequency (generated either from the pin or from routing) for the PLL. CLKI feeds into the Input Clock Divider block. The CLKFB is the feedback signal (generated from CLKOP, CLKOS or from a user clock pin/logic). This signal feeds into the Feedback Divider. The Feedback Divider is used to multiply the reference frequency.

Both the input path and feedback signals enter the Phase Frequency Detect Block (PFD) which detects first for the frequency, and then the phase, of the CLKI and CLKFB are the same which then drives the Voltage Controlled Oscillator (VCO) block. In this block the difference between the input path and feedback signals is used to control the frequency and phase of the oscillator. A LOCK signal is generated by the VCO to indicate that the VCO has locked onto the input clock signal. In dynamic mode, the PLL may lose lock after a dynamic delay adjustment and not relock until the t_{LOCK} parameter has been satisfied.

The output of the VCO then enters the CLKOP divider. The CLKOP divider allows the VCO to operate at higher frequencies than the clock output (CLKOP), thereby increasing the frequency range. The Phase/Duty Cycle/Duty Trim block adjusts the phase and duty cycle of the CLKOS signal. The phase/duty cycle setting can be pre-programmed or dynamically adjusted. A secondary divider takes the CLKOP or CLKOS signal and uses it to derive lower frequency outputs (CLKOK).

The primary output from the CLKOP divider (CLKOP) along with the outputs from the secondary dividers (CLKOK and CLKOK2) and Phase/Duty select (CLKOS) are fed to the clock distribution network.

The PLL allows two methods for adjusting the phase of signal. The first is referred to as Fine Delay Adjustment. This inserts up to 16 nominal 125 ps delays to be applied to the secondary PLL output. The number of steps may be set statically or from the FPGA logic. The second method is referred to as Coarse Phase Adjustment. This allows the phase of the rising and falling edge of the secondary PLL output to be adjusted in 22.5 degree steps. The number of steps may be set statically or from the FPGA logic.



Figure 2-4. General Purpose PLL Diagram



Table 2-4 provides a description of the signals in the PLL blocks.

Table 2-4. PLL Blocks Signal Descriptions

Signal	I/O	Description
CLKI	I	Clock input from external pin or routing
CLKFB	I	PLL feedback input from CLKOP, CLKOS, or from a user clock (pin or logic)
RST	I	"1" to reset PLL counters, VCO, charge pumps and M-dividers
RSTK	I	"1" to reset K-divider
WRDEL	I	DPA Fine Delay Adjust input
CLKOS	0	PLL output to clock tree (phase shifted/duty cycle changed)
CLKOP	0	PLL output to clock tree (no phase shift)
CLKOK	0	PLL output to clock tree through secondary clock divider
CLKOK2	0	PLL output to clock tree (CLKOP divided by 3)
LOCK	0	"1" indicates PLL LOCK to CLKI
FDA [3:0]	I	Dynamic fine delay adjustment on CLKOS output
DRPAI[3:0]	I	Dynamic coarse phase shift, rising edge setting
DFPAI[3:0]	I	Dynamic coarse phase shift, falling edge setting

Delay Locked Loops (DLL)

In addition to PLLs, the LatticeECP3 family of devices has two DLLs per device.

CLKI is the input frequency (generated either from the pin or routing) for the DLL. CLKI feeds into the output muxes block to bypass the DLL, directly to the DELAY CHAIN block and (directly or through divider circuit) to the reference input of the Phase Detector (PD) input mux. The reference signal for the PD can also be generated from the Delay Chain signals. The feedback input to the PD is generated from the CLKFB pin or from a tapped signal from the Delay chain.

The PD produces a binary number proportional to the phase and frequency difference between the reference and feedback signals. Based on these inputs, the ALU determines the correct digital control codes to send to the delay



Primary Clock Routing

The purpose of the primary clock routing is to distribute primary clock sources to the destination quadrants of the device. A global primary clock is a primary clock that is distributed to all quadrants. The clock routing structure in LatticeECP3 devices consists of a network of eight primary clock lines (CLK0 through CLK7) per quadrant. The primary clocks of each quadrant are generated from muxes located in the center of the device. All the clock sources are connected to these muxes. Figure 2-12 shows the clock routing for one quadrant. Each quadrant mux is identical. If desired, any clock can be routed globally.

Figure 2-12. Per Quadrant Primary Clock Selection



Dynamic Clock Control (DCC)

The DCC (Quadrant Clock Enable/Disable) feature allows internal logic control of the quadrant primary clock network. When a clock network is disabled, all the logic fed by that clock does not toggle, reducing the overall power consumption of the device.

Dynamic Clock Select (DCS)

The DCS is a smart multiplexer function available in the primary clock routing. It switches between two independent input clock sources without any glitches or runt pulses. This is achieved regardless of when the select signal is toggled. There are two DCS blocks per quadrant; in total, there are eight DCS blocks per device. The inputs to the DCS block come from the center muxes. The output of the DCS is connected to primary clocks CLK6 and CLK7 (see Figure 2-12).

Figure 2-13 shows the timing waveforms of the default DCS operating mode. The DCS block can be programmed to other modes. For more information about the DCS, please see the list of technical documentation at the end of this data sheet.



Figure 2-13. DCS Waveforms



Figure 2-16. Per Region Secondary Clock Selection



Slice Clock Selection

Figure 2-17 shows the clock selections and Figure 2-18 shows the control selections for Slice0 through Slice2. All the primary clocks and seven secondary clocks are routed to this clock selection mux. Other signals can be used as a clock input to the slices via routing. Slice controls are generated from the secondary clocks/controls or other signals connected via routing.

If none of the signals are selected for both clock and control then the default value of the mux output is 1. Slice 3 does not have any registers; therefore it does not have the clock or control muxes.

Figure 2-17. Slice0 through Slice2 Clock Selection



Figure 2-18. Slice0 through Slice2 Control Selection





For further information, please refer to TN1182, LatticeECP3 sysDSP Usage Guide.

MULT DSP Element

This multiplier element implements a multiply with no addition or accumulator nodes. The two operands, AA and AB, are multiplied and the result is available at the output. The user can enable the input/output and pipeline registers. Figure 2-26 shows the MULT sysDSP element.

Figure 2-26. MULT sysDSP Element



To FPGA Core



MULTADDSUBSUM DSP Element

In this case, the operands AA and AB are multiplied and the result is added/subtracted with the result of the multiplier operation of operands BA and BB of Slice 0. Additionally, the operands AA and AB are multiplied and the result is added/subtracted with the result of the multiplier operation of operands BA and BB of Slice 1. The results of both addition/subtractions are added by the second ALU following the slice cascade path. The user can enable the input, output and pipeline registers. Figure 2-30 and Figure 2-31 show the MULTADDSUBSUM sysDSP element.

Figure 2-30. MULTADDSUBSUM Slice 0









Note: Simplified diagram does not show CE/SET/REST details.

Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysl/O buffers. The blocks on the left and right PIOs contain registers for SDR and full DDR operation. The topside PIO block is the same as the left and right sides except it does not support ODDRX2 gearing of output logic. ODDRX2 gearing is used in DDR3 memory interfaces. The PIO blocks on the bottom contain the SDR registers but do not support generic DDR.

Figure 2-34 shows the Output Register Block for PIOs on the left and right edges.

In SDR mode, OPOSA feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a Dtype or latch. In DDR mode, two of the inputs are fed into registers on the positive edge of the clock. At the next clock cycle, one of the registered outputs is also latched.

A multiplexer running off the same clock is used to switch the mux between the 11 and 01 inputs that will then feed the output.

A gearbox function can be implemented in the output register block that takes four data streams: OPOSA, ONEGA, OPOSB and ONEGB. All four data inputs are registered on the positive edge of the system clock and two of them are also latched. The data is then output at a high rate using a multiplexer that runs off the DQCLK0 and DQCLK1 clocks. DQCLK0 and DQCLK1 are used in this case to transfer data from the system clock to the edge clock domain. These signals are generated in the DQS Write Control Logic block. See Figure 2-37 for an overview of the DQS write control logic.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.

Further discussion on using the DQS strobe in this module is discussed in the DDR Memory section of this data sheet.



Please see TN1177, LatticeECP3 sysIO Usage Guide for on-chip termination usage and value ranges.

Equalization Filter

Equalization filtering is available for single-ended inputs on both true and complementary I/Os, and for differential inputs on the true I/Os on the left, right, and top sides. Equalization is required to compensate for the difficulty of sampling alternating logic transitions with a relatively slow slew rate. It is considered the most useful for the Input DDRX2 modes, used in DDR3 memory, LVDS, or TRLVDS signaling. Equalization filter acts as a tunable filter with settings to determine the level of correction. In the LatticeECP3 devices, there are four settings available: 0 (none), 1, 2 and 3. The default setting is 0. The equalization logic resides in the sysI/O buffers, the two bits of setting is set uniquely in each input IOLOGIC block. Therefore, each sysI/O can have a unique equalization setting within a DQS-12 group.

Hot Socketing

LatticeECP3 devices have been carefully designed to ensure predictable behavior during power-up and powerdown. During power-up and power-down sequences, the I/Os remain in tri-state until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. Please refer to the Hot Socketing Specifications in the DC and Switching Characteristics in this data sheet.

SERDES and PCS (Physical Coding Sublayer)

LatticeECP3 devices feature up to 16 channels of embedded SERDES/PCS arranged in quads at the bottom of the devices supporting up to 3.2Gbps data rate. Figure 2-40 shows the position of the quad blocks for the LatticeECP3-150 devices. Table 2-14 shows the location of available SERDES Quads for all devices.

The LatticeECP3 SERDES/PCS supports a range of popular serial protocols, including:

- PCI Express 1.1
- Ethernet (XAUI, GbE 1000 Base CS/SX/LX and SGMII)
- Serial RapidIO
- SMPTE SDI (3G, HD, SD)
- CPRI
- SONET/SDH (STS-3, STS-12, STS-48)

Each quad contains four dedicated SERDES for high speed, full duplex serial data transfer. Each quad also has a PCS block that interfaces to the SERDES channels and contains protocol specific digital logic to support the standards listed above. The PCS block also contains interface logic to the FPGA fabric. All PCS logic for dedicated protocol support can also be bypassed to allow raw 8-bit or 10-bit interfaces to the FPGA fabric.

Even though the SERDES/PCS blocks are arranged in quads, multiple baud rates can be supported within a quad with the use of dedicated, per channel \div 1, \div 2 and \div 11 rate dividers. Additionally, multiple quads can be arranged together to form larger data pipes.

For information on how to use the SERDES/PCS blocks to support specific protocols, as well on how to combine multiple protocols and baud rates within a device, please refer to TN1176, LatticeECP3 SERDES/PCS Usage Guide.



LatticeECP3 Family Data Sheet DC and Switching Characteristics

April 2014

Data Sheet DS1021

Absolute Maximum Ratings^{1, 2, 3}

Supply Voltage V_CC
Supply Voltage V_{CCAUX} $\ldots \ldots \ldots \ldots -0.5$ V to 3.75 V
Supply Voltage V_{CCJ}
Output Supply Voltage V_{CCIO} –0.5 V to 3.75 V
Input or I/O Tristate Voltage Applied $^4.$ –0.5 V to 3.75 V
Storage Temperature (Ambient)
Junction Temperature (T_J) +125 °C

^{1.} Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

3. All voltages referenced to GND.

4. Overshoot and undershoot of -2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

Recommended Operating Conditions¹

Symbol	Parameter	Min.	Max.	Units
V _{CC} ²	Core Supply Voltage	1.14	1.26	V
V _{CCAUX} ^{2, 4}	Auxiliary Supply Voltage, Terminating Resistor Switching Power Supply (SERDES)	3.135	3.465	V
V _{CCPLL}	PLL Supply Voltage	3.135	3.465	V
V _{CCIO} ^{2, 3}	I/O Driver Supply Voltage	1.14	3.465	V
V _{CCJ} ²	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
V_{REF1} and V_{REF2}	Input Reference Voltage	0.5	1.7	V
V _{TT} ⁵	Termination Voltage	0.5	1.3125	V
t _{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t _{JIND}	Junction Temperature, Industrial Operation	-40	100	°C
SERDES External Pow	er Supply ⁶			
V	Input Buffer Power Supply (1.2 V)	1.14	1.26	V
V CCIB	Input Buffer Power Supply (1.5 V)	1.425	1.575	V
V	Output Buffer Power Supply (1.2 V)	1.14	1.26	V
V CCOB	Output Buffer Power Supply (1.5 V)	1.425	1.575	V
V _{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	1.14	1.26	V

1. For correct operation, all supplies except V_{REF} and V_{TT} must be held in their valid operation range. This is true independent of feature usage.

If V_{CCIO} or V_{CCJ} is set to 1.2 V, they must be connected to the same power supply as V_{CC.} If V_{CCIO} or V_{CCJ} is set to 3.3 V, they must be connected to the same power supply as V_{CCAUX}.

3. See recommended voltages by I/O standard in subsequent table.

4. V_{CCAUX} ramp rate must not exceed 30 mV/µs during power-up when transitioning between 0 V and 3.3 V.

5. If not used, V_{TT} should be left floating.

6. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for information on board considerations for SERDES power supplies.

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LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

			-8				-6		
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
t _{DVECLKGDDR}	Data Hold After CLK	All ECP3EA Devices	0.775		0.775	—	0.775		UI
f _{MAX_GDDR}	DDRX1 Clock Frequency	All ECP3EA Devices		250		250		250	MHz
Generic DDRX2 Inputs with Clock and Data (>10 Bits Wide) Centered at Pin (GDDRX2_RX.ECLK.Centered) Using PCLK Pin for Clock Input									or Clock
Left and Right Sic	les								
t _{SUGDDR}	Data Setup Before CLK	ECP3-150EA	321		403		471		ps
t _{HOGDDR}	Data Hold After CLK	ECP3-150EA	321		403	_	471		ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	_	405	—	325	_	280	MHz
t _{SUGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	321	_	403	—	535	—	ps
t _{HOGDDR}	Data Hold After CLK	ECP3-70EA/95EA	321	_	403	_	535		ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA	_	405		325		250	MHz
t _{SUGDDR}	Data Setup Before CLK	ECP3-35EA	335	_	425	_	535	—	ps
t _{HOGDDR}	Data Hold After CLK	ECP3-35EA	335	—	425	_	535	—	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	_	405	_	325	_	250	MHz
t _{SUGDDR}	Data Setup Before CLK	ECP3-17EA	335	_	425	—	535	—	ps
t _{HOGDDR}	Data Hold After CLK	ECP3-17EA	335	_	425	_	535		ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	_	405		325		250	MHz
Generic DDRX2 Ir	puts with Clock and Data (>10	Bits Wide) Aligned at Pin	(GDDR)	(2_RX.E	CLK.Alig	ned)			
Left and Right Sid	le Using DLLCLKIN Pin for Clo	ck Input							
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-150EA	—	0.225	_	0.225	_	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-150EA	0.775		0.775		0.775		UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	_	460	—	385	—	345	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-70EA/95EA		0.225		0.225		0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-70EA/95EA	0.775		0.775	_	0.775		UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA		460		385		311	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	_	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790		0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	_	460		385		311	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-17EA	—	0.210	—	0.210		0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790	_	0.790	—	0.790	_	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	_	460	_	385	_	311	MHz
Top Side Using P	CLK Pin for Clock Input								
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-150EA	_	0.225	—	0.225	_	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-150EA	0.775	—	0.775		0.775	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	_	235	_	170	_	130	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	_	0.225	_	0.225	_	0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-70EA/95EA	0.775	_	0.775	—	0.775	_	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA	—	235	—	170		130	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	_	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790		0.790	_	0.790		UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	_	235		170	_	130	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-17EA	—	0.210		0.210		0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790		0.790	_	0.790		UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA		235		170		130	MHz

Over Recommended Commercial Operating Conditions



LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

						6			
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
f _{MAX GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	_	250	_	250		250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-35EA	683	_	688		690	_	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-35EA	683	—	688	—	690	_	ps
f _{MAX GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	_	250	_	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-17EA	683	_	688		690		ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-17EA	683	—	688	—	690	_	ps
f _{MAX GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	_	250	_	250	MHz
Generic DDRX1 Ou	tput with Clock and Data Aligne	d at Pin (GDDRX1_TX.	SCLK.Ali	gned) ¹⁰					
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-150EA	—	335	—	338	—	341	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-150EA	—	335	—	338		341	ps
f _{MAX} GDDR	DDRX1 Clock Frequency	ECP3-150EA	_	250	_	250		250	MHz
	Data Invalid Before Clock	ECP3-70EA/95EA	_	339	_	343		347	ps
t _{DIAGDDB}	Data Invalid After Clock	ECP3-70EA/95EA	_	339	_	343		347	ps
f _{MAX} GDDR	DDRX1 Clock Frequency	ECP3-70EA/95EA	_	250	_	250		250	MHz
	Data Invalid Before Clock	ECP3-35EA		322		320		321	ps
	Data Invalid After Clock	ECP3-35EA	_	322	_	320		321	ps
f _{MAX GDDB}	DDRX1 Clock Frequency	ECP3-35EA	_	250	_	250		250	MHz
	Data Invalid Before Clock	ECP3-17EA		322		320		321	ps
	Data Invalid After Clock	ECP3-17EA	_	322	_	320		321	ps
f _{MAX GDDB}	DDRX1 Clock Frequency	ECP3-17EA	_	250	_	250		250	MHz
Generic DDRX1 Ou	Itput with Clock and Data (<10 B	its Wide) Centered at F	in (GDD	RX1_TX.	DQS.Cen	tered) ¹⁰			
Left and Right Side	25		-			-			
t _{DVBGDDR}	Data Valid Before CLK	ECP3-150EA	670		670		670	_	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-150EA	670	_	670	_	670	_	ps
f _{MAX GDDB}	DDRX1 Clock Frequency	ECP3-150EA	_	250	_	250	_	250	MHz
	Data Valid Before CLK	ECP3-70EA/95EA	657		652		650	_	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-70EA/95EA	657	_	652		650	_	ps
f _{MAX GDDB}	DDRX1 Clock Frequency	ECP3-70EA/95EA	_	250	_	250	_	250	MHz
	Data Valid Before CLK	ECP3-35EA	670		675		676	_	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-35EA	670	—	675	—	676	_	ps
f _{MAX GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	_	250	_	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-17EA	670	—	670	—	670	_	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-17EA	670	_	670	_	670	_	ps
f _{MAX} GDDR	DDRX1 Clock Frequency	ECP3-17EA	_	250	_	250		250	MHz
Generic DDRX2 Ou	tput with Clock and Data (>10 B	its Wide) Aligned at Pi	n (GDDR	X2_TX.A	ligned)				
Left and Right Side	es								
t _{DIBGDDR}	Data Invalid Before Clock	All ECP3EA Devices	—	200	—	210	_	220	ps
t _{DIAGDDR}	Data Invalid After Clock	All ECP3EA Devices	—	200	—	210	—	220	ps
f _{MAX GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	_	500	_	420	_	375	MHz
Generic DDRX2 Ou	tput with Clock and Data (>10 B	its Wide) Centered at P	in Using	DQSDL	L (GDDF	X2_TX.C	QSDLL.	Centered)11
Left and Right Side	S								
t _{DVBGDDR}	Data Valid Before CLK	All ECP3EA Devices	400		400		431	_	ps
t _{DVAGDDR}	Data Valid After CLK	All ECP3EA Devices	400	—	400	—	432	—	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz

Over Recommended Commercial Operating Conditions



LatticeECP3 Internal Switching Characteristics^{1, 2, 5} (Continued)

		_	8	-7		-6		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units.
t _{HWREN_EBR}	Hold Write/Read Enable to EBR Memory	0.141		0.145		0.149		ns
t _{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register	0.087		0.096		0.104		ns
t _{HCE_EBR}	Clock Enable Hold Time to EBR Output Register	-0.066		-0.080		-0.094		ns
t _{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register			-0.070		-0.068		ns
t _{HBE_EBR}	Byte Enable Hold Time to EBR Output Register	0.118	_	0.098	_	0.077	_	ns
DSP Block Tin	ning ³							
t _{SUI_DSP}	Input Register Setup Time	0.32	_	0.36	_	0.39	_	ns
t _{HI_DSP}	Input Register Hold Time	-0.17	_	-0.19	_	-0.21	_	ns
t _{SUP_DSP}	Pipeline Register Setup Time	2.23	_	2.30	_	2.37	_	ns
t _{HP_DSP}	Pipeline Register Hold Time	-1.02	_	-1.09	_	-1.15	_	ns
t _{SUO_DSP}	Output Register Setup Time	3.09	_	3.22	_	3.34	_	ns
t _{HO_DSP}	Output Register Hold Time	-1.67	_	-1.76	_	-1.84	_	ns
t _{COI_DSP}	Input Register Clock to Output Time	_	3.05	_	3.35	_	3.73	ns
t _{COP_DSP}	Pipeline Register Clock to Output Time	_	1.30	_	1.47	_	1.64	ns
t _{COO_DSP}	Output Register Clock to Output Time	—	0.58	—	0.60	—	0.62	ns
t _{SUOPT_DSP}	Opcode Register Setup Time	0.31	_	0.35	_	0.39	_	ns
t _{HOPT_DSP}	Opcode Register Hold Time	-0.20	_	-0.24		-0.27	_	ns
t _{SUDATA_DSP}	Cascade_data through ALU to Output Register Setup Time	1.69		1.94		2.14		ns
t _{HPDATA_DSP}	Cascade_data through ALU to Output Register Hold Time	-0.58		-0.80		-0.97		ns

Over Recommended Commercial Operating Conditions

1. Internal parameters are characterized but not tested on every device.

2. Commercial timing numbers are shown. Industrial timing numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

3. DSP slice is configured in Multiply Add/Sub 18 x 18 mode.

4. The output register is in Flip-flop mode.

5. For details on –9 speed grade devices, please contact your Lattice Sales Representative.



LatticeECP3 Family Timing Adders^{1, 2, 3, 4, 5, 7} (Continued)

Buffer Type	Description		-7	-6	Units
RSDS25	RSDS, VCCIO = 2.5 V	-0.07	-0.04	-0.01	ns
PPLVDS	Point-to-Point LVDS, True LVDS, VCCIO = 2.5 V or 3.3 V	-0.22	-0.19	-0.16	ns
LVPECL33	LVPECL, Emulated, VCCIO = 3.3 V	0.67	0.76	0.86	ns
HSTL18_I	HSTL_18 class I 8mA drive, VCCIO = 1.8 V	1.20	1.34	1.47	ns
HSTL18_II	HSTL_18 class II, VCCIO = 1.8 V	0.89	1.00	1.11	ns
HSTL18D_I	Differential HSTL 18 class I 8 mA drive	1.20	1.34	1.47	ns
HSTL18D_II	Differential HSTL 18 class II	0.89	1.00	1.11	ns
HSTL15_I	HSTL_15 class I 4 mA drive, VCCIO = 1.5 V	1.67	1.83	1.99	ns
HSTL15D_I	Differential HSTL 15 class I 4 mA drive	1.67	1.83	1.99	ns
SSTL33_I	SSTL_3 class I, VCCIO = 3.3 V	1.12	1.17	1.21	ns
SSTL33_II	SSTL_3 class II, VCCIO = 3.3 V	1.08	1.12	1.15	ns
SSTL33D_I	Differential SSTL_3 class I	1.12	1.17	1.21	ns
SSTL33D_II	Differential SSTL_3 class II	1.08	1.12	1.15	ns
SSTL25_I	SSTL_2 class I 8 mA drive, VCCIO = 2.5 V	1.06	1.19	1.31	ns
SSTL25_II	SSTL_2 class II 16 mA drive, VCCIO = 2.5 V	1.04	1.17	1.31	ns
SSTL25D_I	Differential SSTL_2 class I 8 mA drive	1.06	1.19	1.31	ns
SSTL25D_II	Differential SSTL_2 class II 16 mA drive	1.04	1.17	1.31	ns
SSTL18_I	SSTL_1.8 class I, VCCIO = 1.8 V	0.70	0.84	0.97	ns
SSTL18_II	SSTL_1.8 class II 8 mA drive, VCCIO = 1.8 V	0.70	0.84	0.97	ns
SSTL18D_I	Differential SSTL_1.8 class I	0.70	0.84	0.97	ns
SSTL18D_II	Differential SSTL_1.8 class II 8 mA drive	0.70	0.84	0.97	ns
SSTL15	SSTL_1.5, VCCIO = 1.5 V	1.22	1.35	1.48	ns
SSTL15D	Differential SSTL_15	1.22	1.35	1.48	ns
LVTTL33_4mA	LVTTL 4 mA drive, VCCIO = 3.3V	0.25	0.24	0.23	ns
LVTTL33_8mA	LVTTL 8 mA drive, VCCIO = 3.3V	-0.06	-0.06	-0.07	ns
LVTTL33_12mA	LVTTL 12 mA drive, VCCIO = 3.3V	-0.01	-0.02	-0.02	ns
LVTTL33_16mA	LVTTL 16 mA drive, VCCIO = 3.3V	-0.07	-0.07	-0.08	ns
LVTTL33_20mA	LVTTL 20 mA drive, VCCIO = 3.3V	-0.12	-0.13	-0.14	ns
LVCMOS33_4mA	LVCMOS 3.3 4 mA drive, fast slew rate	0.25	0.24	0.23	ns
LVCMOS33_8mA	LVCMOS 3.3 8 mA drive, fast slew rate	-0.06	-0.06	-0.07	ns
LVCMOS33_12mA	LVCMOS 3.3 12 mA drive, fast slew rate	-0.01	-0.02	-0.02	ns
LVCMOS33_16mA	LVCMOS 3.3 16 mA drive, fast slew rate	-0.07	-0.07	-0.08	ns
LVCMOS33_20mA	LVCMOS 3.3 20 mA drive, fast slew rate	-0.12	-0.13	-0.14	ns
LVCMOS25_4mA	LVCMOS 2.5 4 mA drive, fast slew rate	0.12	0.10	0.09	ns
LVCMOS25_8mA	LVCMOS 2.5 8 mA drive, fast slew rate	-0.05	-0.06	-0.07	ns
LVCMOS25_12mA	LVCMOS 2.5 12 mA drive, fast slew rate	0.00	0.00	0.00	ns
LVCMOS25_16mA	LVCMOS 2.5 16 mA drive, fast slew rate	-0.12	-0.13	-0.14	ns
LVCMOS25_20mA	LVCMOS 2.5 20 mA drive, fast slew rate	-0.12	-0.13	-0.14	ns
LVCMOS18_4mA	LVCMOS 1.8 4 mA drive, fast slew rate	0.11	0.12	0.14	ns
LVCMOS18_8mA	LVCMOS 1.8 8 mA drive, fast slew rate	0.11	0.12	0.14	ns
LVCMOS18_12mA	LVCMOS 1.8 12 mA drive, fast slew rate	-0.04	-0.03	-0.03	ns
LVCMOS18_16mA	LVCMOS 1.8 16 mA drive, fast slew rate	-0.04	-0.03	-0.03	ns

Over Recommended Commercial Operating Conditions



LatticeECP3 Maximum I/O Buffer Speed ^{1, 2, 3, 4, 5, 6}

Over Recommended Operating Conditions

Buffer	Description	Max.	Units
Maximum Input Frequency		·	
LVDS25	LVDS, $V_{CCIO} = 2.5 V$	400	MHz
MLVDS25	MLVDS, Emulated, V _{CCIO} = 2.5 V	400	MHz
BLVDS25	BLVDS, Emulated, V _{CCIO} = 2.5 V	400	MHz
PPLVDS	Point-to-Point LVDS	400	MHz
TRLVDS	Transition-Reduced LVDS	612	MHz
Mini LVDS	Mini LVDS	400	MHz
LVPECL33	LVPECL, Emulated, V _{CCIO} = 3.3 V	400	MHz
HSTL18 (all supported classes)	HSTL_18 class I, II, V _{CCIO} = 1.8 V	400	MHz
HSTL15	HSTL_15 class I, V _{CCIO} = 1.5 V	400	MHz
SSTL33 (all supported classes)	SSTL_3 class I, II, V _{CCIO} = 3.3 V	400	MHz
SSTL25 (all supported classes)	SSTL_2 class I, II, V _{CCIO} = 2.5 V	400	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, V _{CCIO} = 1.8 V	400	MHz
LVTTL33	LVTTL, V _{CCIO} = 3.3 V	166	MHz
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	166	MHz
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	166	MHz
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	166	MHz
LVCMOS15	LVCMOS 1.5, V _{CCIO} = 1.5 V	166	MHz
LVCMOS12	LVCMOS 1.2, V _{CCIO} = 1.2 V	166	MHz
PCI33	PCI, V _{CCIO} = 3.3 V	66	MHz
Maximum Output Frequency			
LVDS25E	LVDS, Emulated, V _{CCIO} = 2.5 V	300	MHz
LVDS25	LVDS, $V_{CCIO} = 2.5 V$	612	MHz
MLVDS25	MLVDS, Emulated, V _{CCIO} = 2.5 V	300	MHz
RSDS25	RSDS, Emulated, V _{CCIO} = 2.5 V	612	MHz
BLVDS25	BLVDS, Emulated, V _{CCIO} = 2.5 V	300	MHz
PPLVDS	Point-to-point LVDS	612	MHz
LVPECL33	LVPECL, Emulated, V _{CCIO} = 3.3 V	612	MHz
Mini-LVDS	Mini LVDS	612	MHz
HSTL18 (all supported classes)	HSTL_18 class I, II, V _{CCIO} = 1.8 V	200	MHz
HSTL15 (all supported classes)	HSTL_15 class I, V _{CCIO} = 1.5 V	200	MHz
SSTL33 (all supported classes)	SSTL_3 class I, II, V _{CCIO} = 3.3 V	233	MHz
SSTL25 (all supported classes)	SSTL_2 class I, II, V _{CCIO} = 2.5 V	233	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, V _{CCIO} = 1.8 V	266	MHz
LVTTL33	LVTTL, V _{CCIO} = 3.3 V	166	MHz
LVCMOS33 (For all drives)	LVCMOS, 3.3 V	166	MHz
LVCMOS25 (For all drives)	LVCMOS, 2.5 V	166	MHz
LVCMOS18 (For all drives)	LVCMOS, 1.8 V	166	MHz
LVCMOS15 (For all drives)	LVCMOS, 1.5 V	166	MHz
LVCMOS12 (For all drives except 2 mA)	LVCMOS, V _{CCIO} = 1.2 V	166	MHz
LVCMOS12 (2 mA drive)	LVCMOS, V _{CCIO} = 1.2 V	100	MHz



SERDES High-Speed Data Transmitter¹

Table 3-6. Serial Output Timing and Levels

Symbol	Description	Frequency	Min.	Тур.	Max.	Units
V _{TX-DIFF-P-P-1.44}	Differential swing (1.44 V setting) ^{1, 2}	0.15 to 3.125 Gbps	1150	1440	1730	mV, p-p
V _{TX-DIFF-P-P-1.35}	Differential swing (1.35 V setting) ^{1, 2}	0.15 to 3.125 Gbps	1080	1350	1620	mV, p-p
V _{TX-DIFF-P-P-1.26}	Differential swing (1.26 V setting) ^{1, 2}	0.15 to 3.125 Gbps	1000	1260	1510	mV, p-p
V _{TX-DIFF-P-P-1.13}	Differential swing (1.13 V setting) ^{1, 2}	0.15 to 3.125 Gbps	840	1130	1420	mV, p-p
V _{TX-DIFF-P-P-1.04}	Differential swing (1.04 V setting) ^{1, 2}	0.15 to 3.125 Gbps	780	1040	1300	mV, p-p
V _{TX-DIFF-P-P-0.92}	Differential swing (0.92 V setting) ^{1, 2}	0.15 to 3.125 Gbps	690	920	1150	mV, p-p
V _{TX-DIFF-P-P-0.87}	Differential swing (0.87 V setting) ^{1, 2}	0.15 to 3.125 Gbps	650	870	1090	mV, p-p
V _{TX-DIFF-P-P-0.78}	Differential swing (0.78 V setting) ^{1, 2}	0.15 to 3.125 Gbps	585	780	975	mV, p-p
V _{TX-DIFF-P-P-0.64}	Differential swing (0.64 V setting) ^{1, 2}	0.15 to 3.125 Gbps	480	640	800	mV, p-p
V _{OCM}	Output common mode voltage	_	V _{CCOB} -0.75	V _{CCOB} -0.60	V _{CCOB} -0.45	V
T _{TX-R}	Rise time (20% to 80%)	—	145	185	265	ps
T _{TX-F}	Fall time (80% to 20%)	—	145	185	265	ps
Z _{TX-OI-SE}	Output Impedance 50/75/HiZ Ohms (single ended)	_	-20%	50/75/ Hi Z	+20%	Ohms
R _{LTX-RL}	Return loss (with package)	—	10			dB
T _{TX-INTRASKEW}	Lane-to-lane TX skew within a SERDES quad block (intra-quad)	—	_	_	200	ps
T _{TX-INTERSKEW} ³	Lane-to-lane skew between SERDES quad blocks (inter-quad)	_	_	_	1UI +200	ps

1. All measurements are with 50 Ohm impedance.

2. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for actual binary settings and the min-max range.

3. Inter-quad skew is between all SERDES channels on the device and requires the use of a low skew internal reference clock.



SERDES High Speed Data Receiver

Table 3-9. Serial Input Data Specifications

Symbol	Description			Тур.	Max.	Units	
		3.125 G	—	—	136		
		2.5 G	—	—	144		
	Stream of nontransitions ¹	1.485 G	—	—	160	Bits	
RX-CID _S	(CID = Consecutive Identical Digits) @ 10 ⁻¹² BER	622 M	—	—	204		
		270 M	—	—	228		
		150 M	—	—	296		
V _{RX-DIFF-S}	Differential input sensitivity		150	—	1760	mV, p-p	
V _{RX-IN}	Input levels		0	—	V _{CCA} +0.5 ⁴	V	
V _{RX-CM-DC}	Input common mode range (DC coupled)		0.6	—	V _{CCA}	V	
V _{RX-CM-AC}	Input common mode range (AC coupled) ³		0.1	—	V _{CCA} +0.2	V	
T _{RX-RELOCK}	SCDR re-lock time ²	—	1000	—	Bits		
Z _{RX-TERM}	Input termination 50/75 Ohm/High Z	-20%	50/75/HiZ	+20%	Ohms		
RL _{RX-RL}	Return loss (without package)		10	—	—	dB	

1. This is the number of bits allowed without a transition on the incoming data stream when using DC coupling.

2. This is the typical number of bit times to re-lock to a new phase or frequency within +/- 300 ppm, assuming 8b10b encoded data.

3. AC coupling is used to interface to LVPECL and LVDS. LVDS interfaces are found in laser drivers and Fibre Channel equipment. LVDS interfaces are generally found in 622 Mbps SERDES devices.

4. Up to 1.76 V.

Input Data Jitter Tolerance

A receiver's ability to tolerate incoming signal jitter is very dependent on jitter type. High speed serial interface standards have recognized the dependency on jitter type and have specifications to indicate tolerance levels for different jitter types as they relate to specific protocols. Sinusoidal jitter is considered to be a worst case jitter type.

Description	Frequency	Condition	Min.	Тур.	Max.	Units
Deterministic		600 mV differential eye	—	_	0.47	UI, p-p
Random	3.125 Gbps	600 mV differential eye	—	_	0.18	UI, p-p
Total	600 mV differential eye — — —			0.65	UI, p-p	
Deterministic		600 mV differential eye	—	_	0.47	UI, p-p
Random	2.5 Gbps	600 mV differential eye	—	_	0.18	UI, p-p
Total		600 mV differential eye	—		0.65	UI, p-p
Deterministic		600 mV differential eye	—	_	0.47	UI, p-p
Random	1.25 Gbps	600 mV differential eye	—	_	0.18	UI, p-p
Total		600 mV differential eye	—	_	0.65	UI, p-p
Deterministic		600 mV differential eye	—	_	0.47	UI, p-p
Random	622 Mbps	600 mV differential eye	—	_	0.18	UI, p-p
Total]	600 mV differential eye	—	—	0.65	UI, p-p

Table 3-10. Receiver Total Jitter Tolerance Specification

Note: Values are measured with CJPAT, all channels operating, FPGA Logic active, I/Os around SERDES pins quiet, voltages are nominal, room temperature.



Table 3-11. Periodic Receiver Jitter Tolerance Specification

Description	Frequency	Condition	Min.	Тур.	Max.	Units
Periodic	2.97 Gbps	600 mV differential eye	_	_	0.24	UI, p-p
Periodic	2.5 Gbps	600 mV differential eye	_	—	0.22	UI, p-p
Periodic	1.485 Gbps	600 mV differential eye	—	—	0.24	UI, p-p
Periodic	622 Mbps	600 mV differential eye	_	_	0.15	UI, p-p
Periodic	150 Mbps	600 mV differential eye	_		0.5	UI, p-p

Note: Values are measured with PRBS 2⁷–1, all channels operating, FPGA Logic active, I/Os around SERDES pins quiet, voltages are nominal, room temperature.



LatticeECP3 sysCONFIG Port Timing Specifications (Continued)

Over Recommended Operating Conditions

Parameter	Description	Min.	Max.	Units
t _{SSCL}	CCLK Minimum Low Pulse	5		ns
t _{HLCH}	HOLDN Low Setup Time (Relative to CCLK)	5	_	ns
t _{CHHH}	HOLDN Low Hold Time (Relative to CCLK)	5	_	ns
Master and				
t _{CHHL}	HOLDN High Hold Time (Relative to CCLK)	5	_	ns
t _{HHCH}	HOLDN High Setup Time (Relative to CCLK)	5		ns
t _{HLQZ}	HOLDN to Output High-Z	_	9	ns
t _{HHQX}	HOLDN to Output Low-Z	_	9	ns

1. Re-toggling the PROGRAMN pin is not permitted until the INITN pin is high. Avoid consecutive toggling of the PROGRAMN.

Parameter	Min.	Max.	Units
Master Clock Frequency	Selected value - 15%	Selected value + 15%	MHz
Duty Cycle	40	60	%

Figure 3-20. sysCONFIG Parallel Port Read Cycle





Pin Information Summary (Cont.)

Pin Information	n Summary ECP3-70EA			
Pin T	уре	484 fpBGA	672 fpBGA	1156 fpBGA
	Bank 0	21	30	43
	Bank 1	18	24	39
	Bank 2	8	12	13
Emulated Differential	Bank 3	20	23	33
	Bank 6	22	25	33
	Bank 7	11	16	18
	Bank 8	12	12	12
	Bank 0	0	0	0
	Bank 1	0	0	0
	Bank 2	6	9	9
High-Speed Differential I/	Bank 3	9	12	16
	Bank 6	11	14	16
	Bank 7	9	12	13
	Bank 8	0	0	0
	Bank 0	42/21	60/30	86/43
	Bank 1	36/18	48/24	78/39
Total Single-Ended/ Total Differential I/O per Bank	Bank 2	28/14	42/21	44/22
	Bank 3	58/29	71/35	98/49
	Bank 6	67/33	78/39	98/49
	Bank 7	40/20	56/28	62/31
	Bank 8	24/12	24/12	24/12
	Bank 0	3	5	7
	Bank 1	3	4	7
	Bank 2	2	3	3
DDR Groups Bonded	Bank 3	3	4	5
por Dank	Bank 6	4	4	5
	Bank 7	3	4	4
	Configuration Bank 8	0	0	0
SERDES Quads		1	2	3

1. Some DQS groups may not support DQS-12. Refer to the device pinout (.csv) file.



Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672C	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672C	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672C	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6LFN672C	1.2 V	-6	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7LFN672C	1.2 V	-7	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8LFN672C	1.2 V	-8	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156C	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156C	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156C	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-6LFN1156C	1.2 V	-6	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7LFN1156C	1.2 V	-7	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8LFN1156C	1.2 V	-8	LOW	Lead-Free fpBGA	1156	COM	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672CTW ¹	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672CTW ¹	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672CTW ¹	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156CTW1	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156CTW1	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156CTW1	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	149

1. Note: Specifications for the LFE3-150EA-*sp*FN*pkg*CTW and LFE3-150EA-*sp*FN*pkg*ITW devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*sp*FN*pkg*C and LFE3-150EA-*sp*FN*pkg*I devices respectively, except as specified below.

• The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.

• The SERDES XRES pin on the TW device passes CDM testing at 250 V.